Accepted Manuscript

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PII: S0925-8388(18)33008-1

DOI: 10.1016/j.jallcom.2018.08.125

Reference: JALCOM 47213

To appear in: Journal of Alloys and Compounds

Received Date: 8 May 2018

Revised Date: 11 August 2018 Accepted Date: 15 August 2018

Please cite this article as: B. Tiss, M. Erouel, N. Bouguila, M. Kraini, K. Khirouni, Effect of silver doping on structural and optical properties of In₂S₃ thin films fabricated by chemical pyrolysis, *Journal of Alloys and Compounds* (2018), doi: 10.1016/j.jallcom.2018.08.125.

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Effect of silver doping on structural and optical properties of In_2S_3 thin films fabricated by chemical pyrolysis

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Abstract

Silver doped indium sulphide thin films (In_2S_3 :Ag) were deposited by spray pyrolysis technique on glass substrates at temperature 350 °C. The films were prepared by varying the Ag:In ratio from 0% to 8%. The effect of silver concentration on structural and optical properties of In_2S_3 :Ag thin films have been studied in detail using X-ray diffraction (XRD) and ultra violet, visible and near infra red (UV-Vis-NIR) transmittance spectroscopy. The X-ray diffraction analysis showed that the prepared layers are polycrystalline and crystallize in a β -In₂S₃ cubic structure and the size of the crystallites varies between 16 to 20 nm. UV-Vis-NIR spectroscopy measurements revealed that the optical transmittance of the films exceeds 90% in the visible and near infrared region and also the direct band gap energy of the fabricated thin film samples increases with doping from 2.63 to 2.97 eV. The roughness values evaluated are almost constant for different doping concentration.

Key-words: In₂S₃ thin films, Ag doping, spray pyrolysis, X-ray diffraction, Transmittance spectroscopy.

1. Introduction

Thin films of toxic cadmium sulfide (CdS) were used as a buffer layer for Cu(In,Ga)Se, CuInSe₂ and CuInS₂ solar cells, and play a vital role in enhancing the efficiency up to 20% [1]. Hence, the interest of using non toxic films like In₂S₃ [2] due to its eco-friendly nature and its wide energy band gap varying from 2 to 2.75 eV [2-7] and photoconductive behavior [8].

Indium sulfide is one of the important n-type semiconductor materials for group (III-VI). The films fabricated using this material attract an intense interest due to their high photocatalysis characteristics under ambient conditions, photosensitivity and photoconductivity [9-12].

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